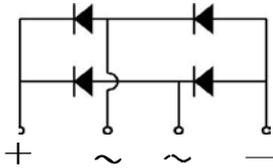


Low VF Bridge Rectifiers

GBJ



Features

- Glass Passivated Chip Junction
- Low IRRM
- Ultra Low VF
- High VRRM

Benefits

- Case: GBJ
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor
- Reduced snubbing

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	GBJ1506L		Units	
Maximum Repetitive Peak Reverse Voltage	VRRM	600		V	
Maximum RMS voltage	VRMS	420		V	
Maximum DC Blocking Voltage	VDC	600		V	
Average Rectified Output Current	I_o	15.0		A	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	300		A	
Instantaneous forward voltage per diode@25 °C	VF	TYP.	MAX.	V	
		IF=3A	0.85		0.89
		IF=7.5A	0.92		0.96
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	10	500	μA	
Typical Junction Capacitance (Note1)	Cj	25		pF	
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150		°C	

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

Fig.1 Current Derating, Case

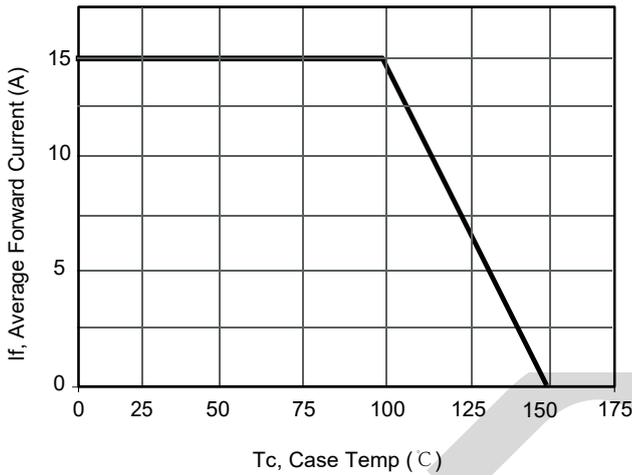


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

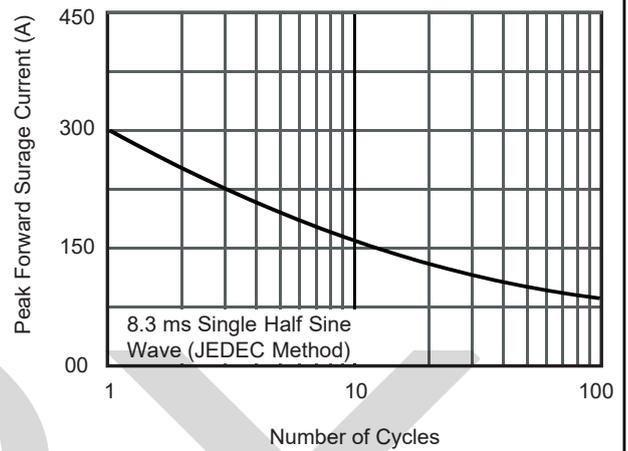


Fig.3 Typical Forward Voltage

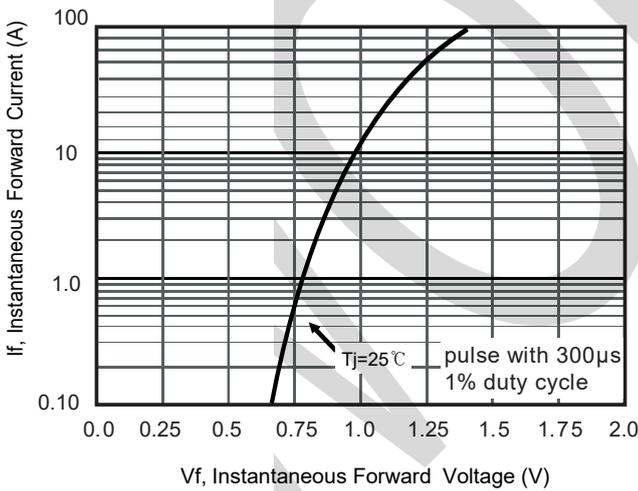
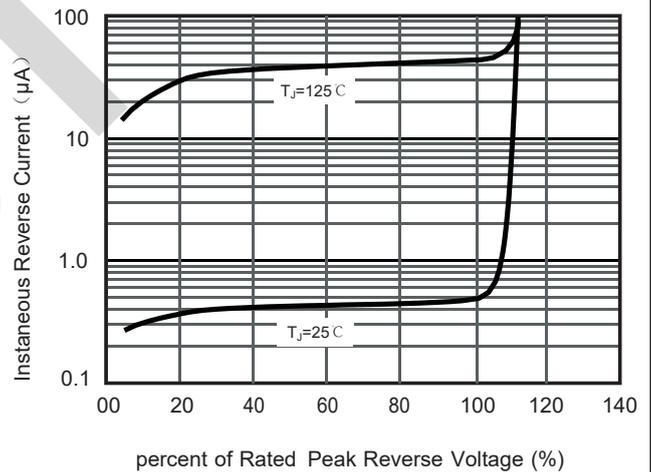
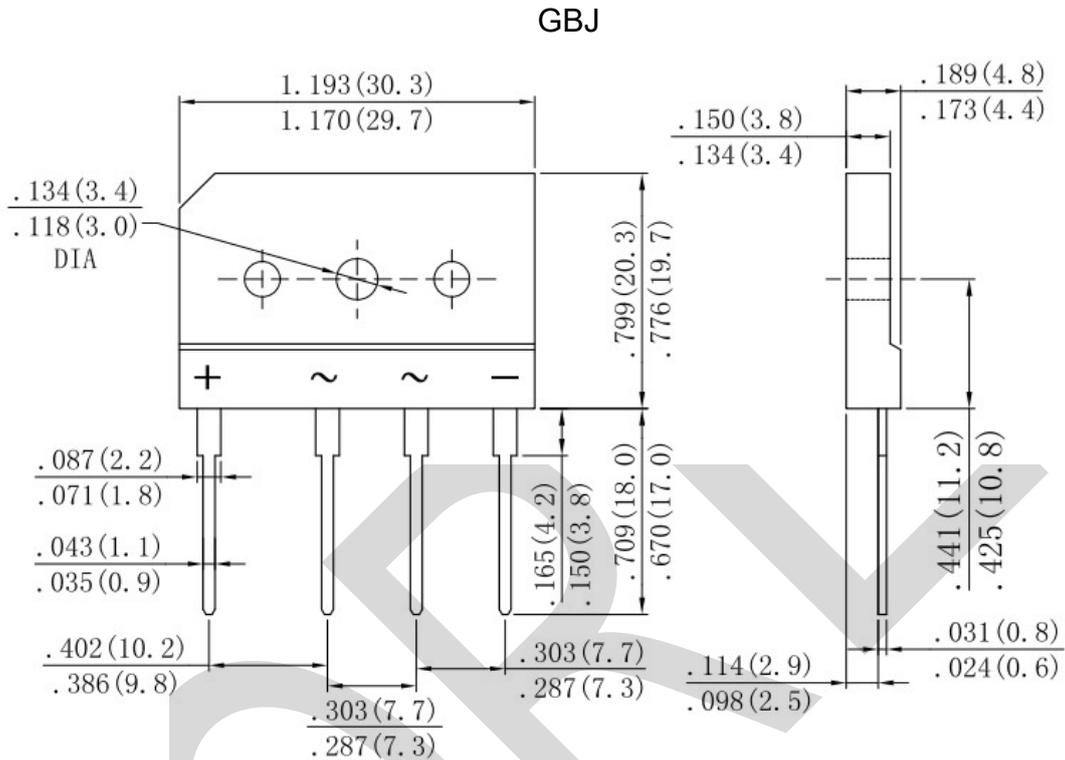


Fig.4 Typical Reverse Characteristics



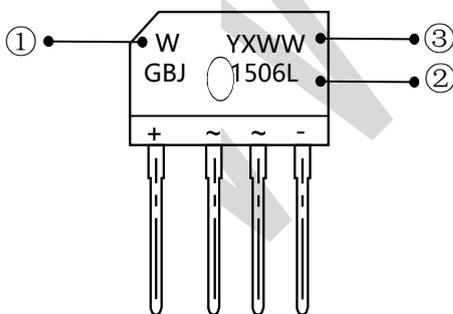
PACKAGE OUTLINE DIMENSIONS

Note:unit In(mm)



Dimensions in inches and(millimeters)

Marking Information



①W : Company's trademark

②Product model : GBJ1506L

③PDC information :

Y X WW

WW:Week code(01 to 53)

X:Internal identification code

Y:Year code(ex:0=2020)